

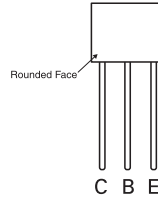
E-LINE PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

FEATURES

- Excellent h_{FE} characteristics up to $I_C=50mA$
- Low Saturation voltages

PARTMARKING

ZTX
560



PIN-OUT



E-LINE

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | VALUE | UNIT |
|---|----------------|-------------|------|
| Collector-base voltage | V_{CBO} | -500 | V |
| Collector-emitter voltage | V_{CEO} | -500 | V |
| Emitter-base voltage | V_{EBO} | -5 | V |
| Peak pulse current | I_{CM} | -500 | mA |
| Continuous collector current | I_C | -150 | mA |
| Power dissipation | P_{tot} | 1 | W |
| Operating and storage temperature range | $T_j; T_{stg}$ | -55 to +150 | °C |

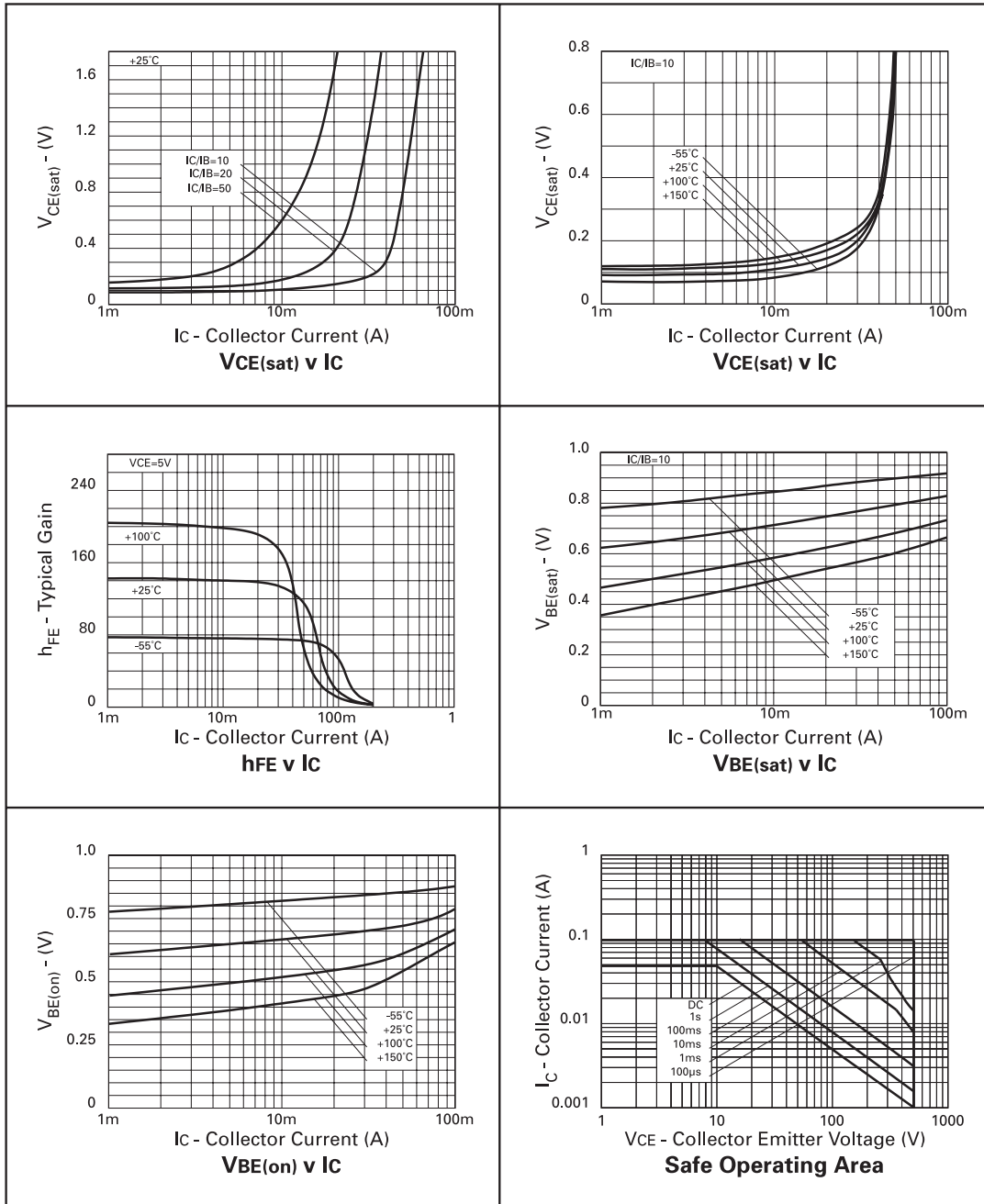
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$)

| PARAMETER | SYMBOL | MIN. | MAX. | UNIT | CONDITIONS |
|---------------------------------------|-----------------------|---------------------|----------------------|---------------|--|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | -500 | | V | $I_C = -100\mu A$ |
| Collector-emitter breakdown voltage | $V_{BR(CEO)}$ | -500 | | V | $I_C = -10mA^*$ |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | -5 | | V | $I_E = -100\mu A$ |
| Collector cut-off current | $I_{CBO}; I_{CES}$ | | -100 | nA | $V_{CB} = -500V; V_{CE} = -500V$ |
| Emitter cut-off current | I_{EBO} | | -100 | nA | $V_{EB} = -5V$ |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | | -0.2 -0.5 | V | $I_C = -20mA, I_B = -2mA^*$ $I_C = -50mA, I_B = -10mA^*$ |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | | -0.9 | V | $I_C = -50mA, I_B = -10mA^*$ |
| Base-emitter turn on voltage | $V_{BE(on)}$ | | -0.9 | V | $I_C = -50mA, V_{CE} = -10V^*$ |
| Static forward current transfer ratio | h_{FE} | 100 80 15 typ | 300 300 | | $I_C = -1mA, V_{CE} = -10V$ $I_C = -50mA, V_{CE} = -10V^*$ $I_C = -100mA, V_{CE} = -10V^*$ |
| Transition frequency | f_T | 60 | | MHz | $V_{CE} = -20V, I_C = -10mA, f = 50MHz$ |
| Output capacitance | C_{obo} | | 8 | pF | $V_{CB} = -20V, f = 1MHz$ |
| Switching times | t_{on} t_{off} | | 110 typ. 1.5 typ. | ns μs | $V_{CE} = -100V, I_C = -50mA, I_{B1} = -5mA, I_{B2} = 10mA$ |

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

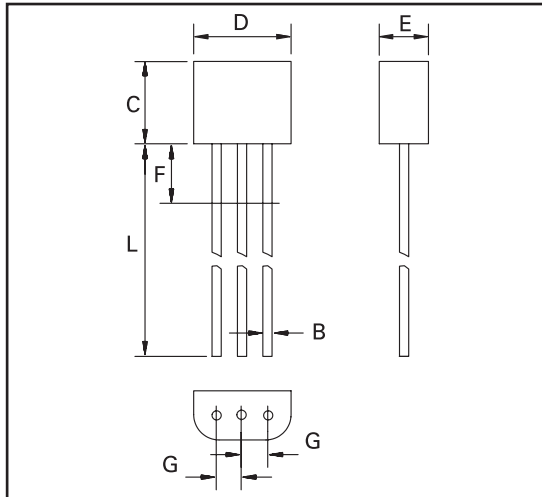
ZTX560

TYPICAL CHARACTERISTICS



ZTX560

PACKAGE OUTLINE



PACKAGE DIMENSIONS

| DIM | Millimeters | | Inches | |
|-----|-------------|-------|-----------|--------|
| | Min | Max | Min | Max |
| A | 0.41 | 0.495 | 0.016 | 0.0195 |
| B | 0.41 | 0.495 | 0.016 | 0.0195 |
| C | 3.61 | 4.01 | 0.142 | 0.158 |
| D | 4.37 | 4.77 | 0.172 | 0.188 |
| E | 2.16 | 2.41 | 0.085 | 0.095 |
| F | — | 2.50 | — | 0.098 |
| G | 1.27 NOM | | 0.050 NOM | |
| L | 13.00 | 13.97 | 0.512 | 0.550 |

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ISSUE 2 - SEPTEMBER 2006

